

BAS32L

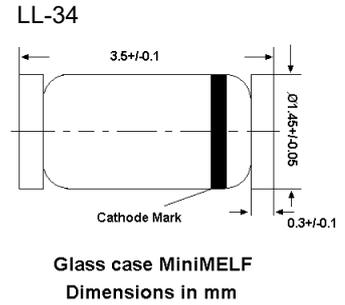
Silicon Epitaxial Planar Switching Diode

Features

- Small hermetically-sealed glass SMD package
- High switching speed

Application

- High-speed switching
- Fast logic applications



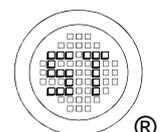
Absolute Maximum Ratings ($T_a = 25\text{ °C}$)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	100	V
Continuous Reverse Voltage	V_R	75	V
Continuous Forward Current	I_F	200	mA
Repetitive Peak Forward Current	I_{FRM}	450	mA
Non-repetitive Peak Forward Surge Current	I_{FSM}	0.5 1 4	A
		at $t = 1\text{ s}$ at $t = 1\text{ ms}$ at $t = 1\text{ }\mu\text{s}$	
Power dissipation	P_{tot}	500	mW
Junction temperature	T_j	175	°C
Storage temperature range	T_{stg}	- 65 to + 175	°C

Thermal Characteristics

Parameter	Symbol	Max.	Unit
Thermal Resistance from Junction Ambient ¹⁾	$R_{\theta JA}$	300	°C/W

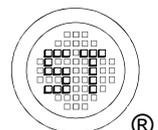
¹⁾ Valid provided that electrodes are kept at ambient temperature.



BAS32L

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at $I_F = 5\text{ mA}$	V_F	620	750	mV
at $I_F = 100\text{ mA}$	V_F	-	1000	mV
at $I_F = 100\text{ mA}, T_j = 100\text{ }^\circ\text{C}$	V_F	-	930	mV
Reverse Current at $V_R = 20\text{ V}$	I_R	-	25	nA
at $V_R = 75\text{ V}$	I_R	-	5	μA
at $V_R = 20\text{ V}, T_j = 150\text{ }^\circ\text{C}$	I_R	-	50	μA
at $V_R = 75\text{ V}, T_j = 150\text{ }^\circ\text{C}$	I_R	-	100	μA
Reverse Breakdown Voltage at $I_R = 100\text{ }\mu\text{A}$	$V_{(BR)R}$	100	-	V
Diode Capacitance at $V_R = 0, f = 1\text{ MHz}$	C_d	-	2	pF
Reverse Recovery Time at $I_F = 10\text{ mA}, I_{rr} = 0.1 \times I_R, V_R = 6\text{ V}, R_L = 100\text{ }\Omega$	t_{rr}	-	4	ns



BAS32L

Electrical Characteristics Curves

Fig 1. Forward Characteristics

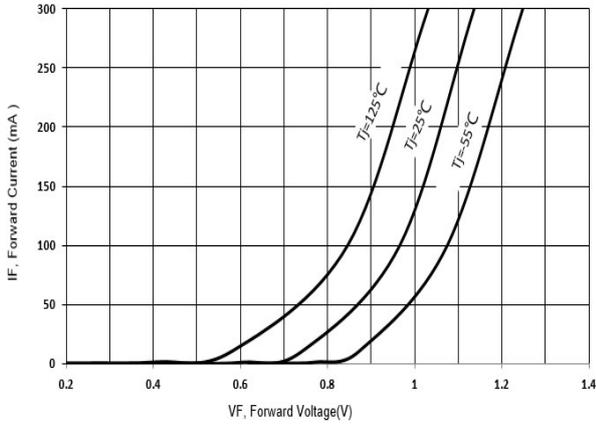


Fig 2. Reverse Characteristics

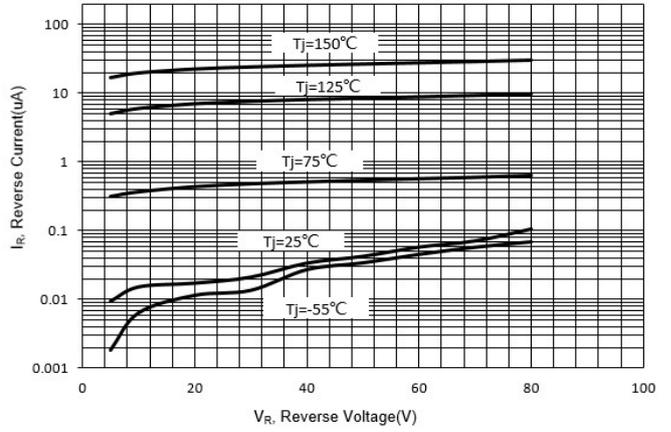


Fig 3. Junction Capacitance

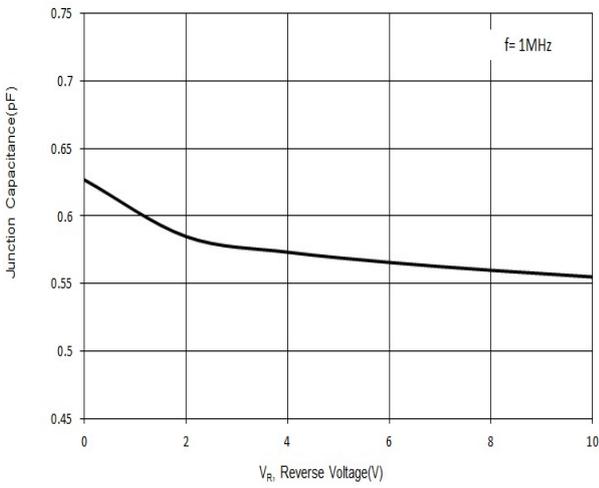


Fig 4. Power Derating Curves

